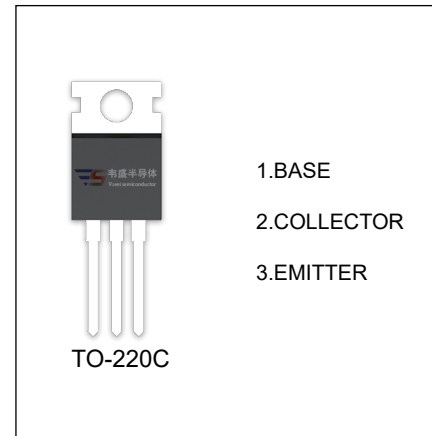


## 2SB1375 TRANSISTOR (PNP)

### FEATURES

- High Power Dissipation:  $P_C=25W(T_C=25^{\circ}C)$
- Low voltage:  $V_{CE(sat)}=-1.5V(Max)(I_C=-2A, I_B=-0.2A)$
- Collector Metal(Fin)is Coverd with Mold Resin
- Complementary to 2SD2012



### MAXIMUM RATINGS ( $T_a=25^{\circ}C$ unless otherwise noted )

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current -Continuous	-3	A
$P_C$	Collector Dissipation	2	W
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60V, I_E=0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-7V, I_C=0$			-10	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-0.5A$	100		320	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-2A$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5V, I_C=-0.5A$			-1	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-0.5A$		9		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		50		pF